

# Crystallinity of Sacrificial Etch Layer Influences Resulting Structure During Simultaneous Deposition and Etching

<sup>1</sup>Hannah R. M. Margavio, <sup>1</sup>Landon Keller, <sup>2</sup>Noel Arellano, <sup>2</sup>Rudy Wojtecki, <sup>1</sup>Gregory N. Parsons

<sup>1</sup>Department of Chemical and Biomolecular Engineering, North Carolina State University, Raleigh, NC

<sup>2</sup>IBM Almaden, San Jose, CA

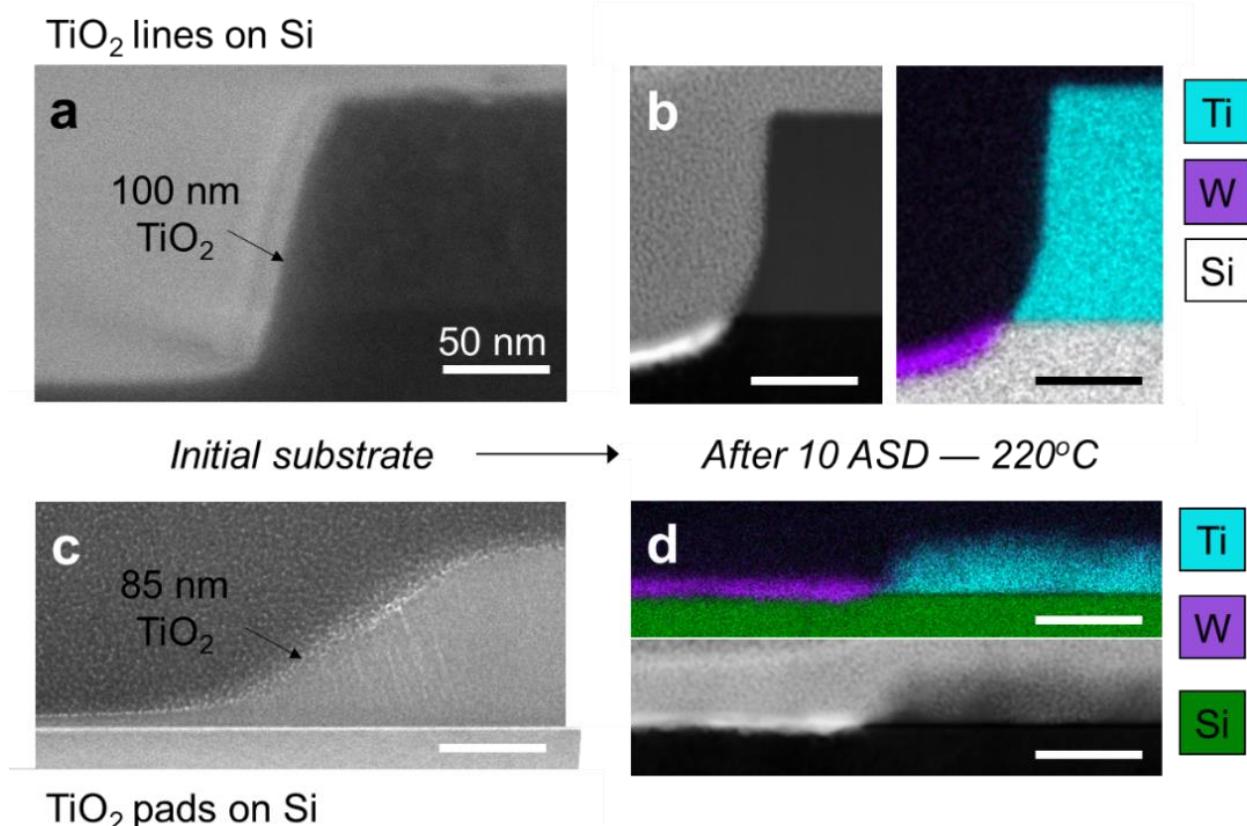


Figure 1: (a) Cross-sectional SEM image of starting substrate (i) consisting of 100 nm thick TiO<sub>2</sub> lines on Si. (b) HAADF STEM and STEM EDS elemental map of substrate (i) exposed to 10 W ASD cycles at 220°C. (c) Bright field TEM image of starting substrate (ii). (d) HAADF STEM image and STEM EDS elemental map of substrate (ii) after 10 W ASD cycles.